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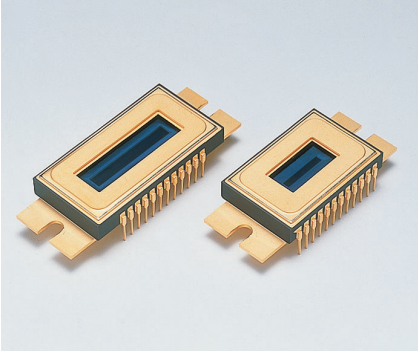
CCD area image sensor



S7030/S7031 series

Back-thinned FFT-CCD

The S7030/S7031 series is a family of FFT-CCD image sensors specifically designed for low-light-level detection in scientific applications. By using the binning operation, the S7030/S7031 series can be used as a linear image sensor having a long aperture in the direction of the device length. This makes the S7030/S7031 series suited for use in spectrophotometry. The binning operation offers significant improvement in S/N and signal processing speed compared with conventional methods by which signals are digitally added by an external circuit. The S7030/S7031 series also features low noise and low dark signal (MPP mode operation). This enables low-light-level detection and long integration time, thus achieving a wide dynamic range.
The S7030/S7031 series has an effective pixel size of 24 × 24 µm and is available in image areas ranging from 12.288 (H) × 1.392 (V) mm^2 (512 × 58 pixels) up to a large image area of 24.576 (H) × 2.928 (V) mm^2 (1024 × 250 pixels).

Features

- **Non-cooled type: S7030 series**
  One-stage TE-cooled type: S7031 series
- **Pixel size: 24 × 24 µm**
- **Line, pixel binning**
- **Greater than 90% quantum efficiency at peak sensitivity wavelength**
- **Wide spectral response range**
- **Low readout noise**
- **Wide dynamic range**
- **MPP operation**
- **High UV sensitivity with good stability**

Applications

- **Fluorescence spectrometer, ICP**
- **Industrial inspection**
- **Semiconductor inspection**
- **DNA sequencer**
- **Low-light-level detection**
- **Raman spectrometer**

Selection guide

Type no.	Cooling	Number of total pixels	Number of effective pixels	Image size [mm (H) × mm (V)]	Suitable multichannel detector head
S7030-0906	Non-cooled	532 × 64	512 × 58	12.288 × 1.392	C7040
S7030-0907		532 × 128	512 × 122	12.288 × 2.928	
S7030-1006		1044 × 64	1024 × 58	24.576 × 1.392	
S7030-1007		1044 × 128	1024 × 122	24.576 × 2.928	
S7031-0906S	One-stage TE-cooled	532 × 64	512 × 58	12.288 × 1.392	C7041
S7031-0907S		532 × 128	512 × 122	12.288 × 2.928	
S7031-1006S		1044 × 64	1024 × 58	24.576 × 1.392	
S7031-1007S		1044 × 128	1024 × 122	24.576 × 2.928	

Note: Two-stage TE-cooled type (S7032-1006/-1007) is available upon request (made-to-order product).

Structure

Parameter	S7030 series	S7031 series
Pixel size (H × V)	24 × 24 µm	
Vertical clock phase	2 phases	
Horizontal clock phase	2 phases	
Output circuit	One-stage MOSFET source follower	
Package	24-pin ceramic DIP (refer to dimensional outlines)	
Window*1	Quartz glass*2	AR-coated sapphire*3

*1: Temporary window type (ex. S7030-0906N) is available upon request.
(Temporary window is fixed by tape to protect the CCD chip and wire bonding.)
*2: Resing sealing
*3: Hermetic sealing

Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Min.	Typ.	Max.	Unit
Operating temperature*4	Topr	-50	-	+50	°C
Storage temperature	Tstg	-50	-	+70	°C
Output transistor drain voltage	V_{OD}	-0.5	-	+25	V
Reset drain voltage	V_{RD}	-0.5	-	+18	V
Vertical input source voltage	V_{ISV}	-0.5	-	+18	V
Horizontal input source voltage	V_{ISH}	-0.5	-	+18	V
Vertical input gate voltage	V_{IG1V}, V_{IG2V}	-10	-	+15	V
Horizontal input gate voltage	V_{IG1H}, V_{IG2H}	-10	-	+15	V
Summing gate voltage	V_{SG}	-10	-	+15	V
Output gate voltage	V_{OG}	-10	-	+15	V
Reset gate voltage	V_{RG}	-10	-	+15	V
Transfer gate voltage	V_{TG}	-10	-	+15	V
Vertical shift register clock voltage	V_{P1V}, V_{P2V}	-10	-	+15	V
Horizontal shift register clock voltage	V_{P1H}, V_{P2H}	-10	-	+15	V

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.
*4: Package temperature (S7030 series), chip temperature (S7031 series)

Operating conditions (MPP mode, Ta=25 °C)

Parameter			Symbol	Min.	Typ.	Max.	Unit
Output transistor drain voltage			V_{OD}	18	20	22	V
Reset drain voltage			V_{RD}	11.5	12	12.5	V
Output gate voltage			V_{OG}	1	3	5	V
Substrate voltage			V_{SS}	-	0	-	V
Test point	vertical input source		V_{ISV}	-	V_{RD}	-	V
	horizontal input source		V_{ISH}	-	V_{RD}	-	V
	vertical input gate		V_{IG1V}, V_{IG2V}	-9	-8	-	V
	horizontal input gate		V_{IG1H}, V_{IG2H}	-9	-8	-	V
Vertical shift register clock voltage		High	V_{P1VH}, V_{P2VH}	4	6	8	V
		Low	V_{P1VL}, V_{P2VL}	-9	-8	-7	
Horizontal shift register clock voltage		High	V_{P1HH}, V_{P2HH}	4	6	8	V
		Low	V_{P1HL}, V_{P2HL}	-9	-8	-7	
Summing gate voltage		High	V_{SGH}	4	6	8	V
		Low	V_{SGL}	-9	-8	-7	
Reset gate voltage		High	V_{RGH}	4	6	8	V
		Low	V_{RGL}	-9	-8	-7	
Transfer gate voltage		High	V_{TGH}	4	6	8	V
		Low	V_{TGL}	-9	-8	-7	
External load resistance			R_L	20	22	24	kΩ

Electrical characteristics (Ta=25 °C)

Parameter		Symbol	Min.	Typ.	Max.	Unit
Signal output frequency		fc	-	0.25	1	MHz
Vertical shift register capacitance	S703*-0906	C_{P1V}, C_{P2V}	-	750	-	pF
	S703*-0907/-1006		-	1500	-	
	S703*-1007		-	3000	-	
Horizontal shift register capacitance	S703*-0906/-0907	C_{P1H}, C_{P2H}	-	110	-	pF
	S703*-1006/-1007			180		
Summing gate capacitance		C_{SG}	-	30	-	pF
Reset gate capacitance		C_{RG}	-	30	-	pF
Transfer gate capacitance	S703*-0906/-0907	C_{TG}	-	55	-	pF
	S703*-1006/-1007			75		
Charge transfer efficiency*5		CTE	0.99995	0.99999	-	-
DC output level*6		Vout	14	16	18	V
Output impedance*6		Zo	-	3	4	kΩ
Power consumption*6 *7		P	-	13	14	mW

*5: Charge transfer efficiency per pixel, measured at half of the full well capacity
*6: The values depend on the load resistance. (Typical, V_{OD}=20 V, Load resistance=22 kΩ)
*7: Power consumption of the on-chip amplifier plus load resistance

Electrical and optical characteristics (Ta=25 °C, unless otherwise noted)

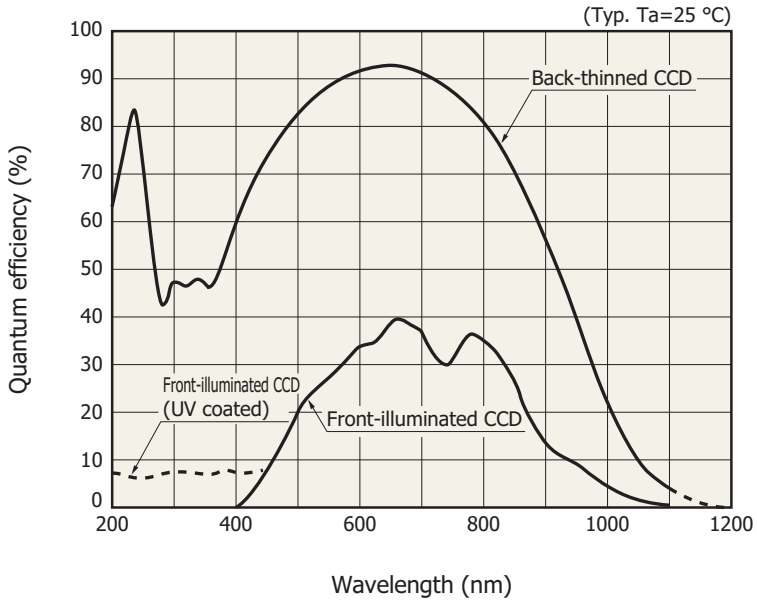
Parameter			Symbol	Min.	Typ.	Max.	Unit
Saturation output voltage			Vsat	-	Fw × Sv	-	V
Full well capacity	Vertical		Fw	240	320	-	ke^-
	Horizontal*8			800	1000	-	
CCD node sensitivity			Sv	1.8	2.2	-	$\mu V/e^-$
Dark current*9 (MPP mode)	25 °C		DS	-	100	1000	e^-/pixel/s
	0 °C			-	10	100	
Readout noise*10			Nr	-	8	16	e^- rms
Dynamic range*11	Line binning		DR	100000	125000	-	-
	Area scanning			30000	40000	-	-
Photoresponse nonuniformity*12			PRNU	-	±3	±10	%
Spectral response range			λ	-	200 to 1100	-	nm
Blemish	Point defect*13	White spots	-	-	-	0	-
		Black spots		-	-	10	-
	Cluster defect*14			-	-	3	-
	Column defect*15			-	-	0	-

*8: The linearity is ±1.5%.
*9: Dark current nearly doubles for every 5 to 7 °C increase in temperature.
*10: Measured with a HAMAMATSU C4880 digital CCD camera with a CDS circuit (sensor temperature: -40 °C, operating frequency: 150 kHz)
*11: Dynamic range = Full well capacity / Readout noise
*12: Measured at one-half of the saturation output (full well capacity) using LED light (peak emission wavelength: 560 nm)

$$\text{Photoresponse nonuniformity} = \frac{\text{Fixed pattern noise (peak to peak)}}{\text{Signal}} \times 100 \ [\%]$$

*13: White spots
Pixels whose dark current is higher than 1 ke^- after one-second integration at 0 °C.
Black spots
Pixels whose sensitivity is lower than one-half of the average pixel output. (measured with uniform light producing one-half of the saturation charge)
*14: 2 to 9 contiguous defective pixels
*15: 10 or more contiguous defective pixels

Spectral response (without window)*16



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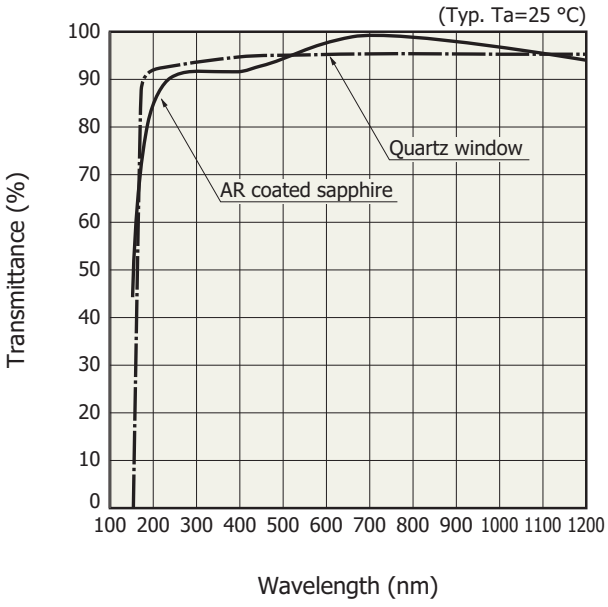
*16: Spectral response with quartz glass or AR-coated sapphire is decreased according to the spectral transmittance characteristic of window material.

Spectral transmittance characteristics



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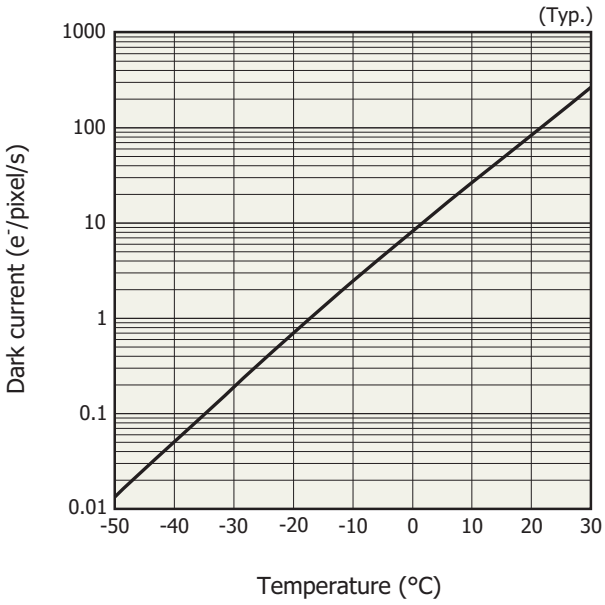
Dark current vs. temperature



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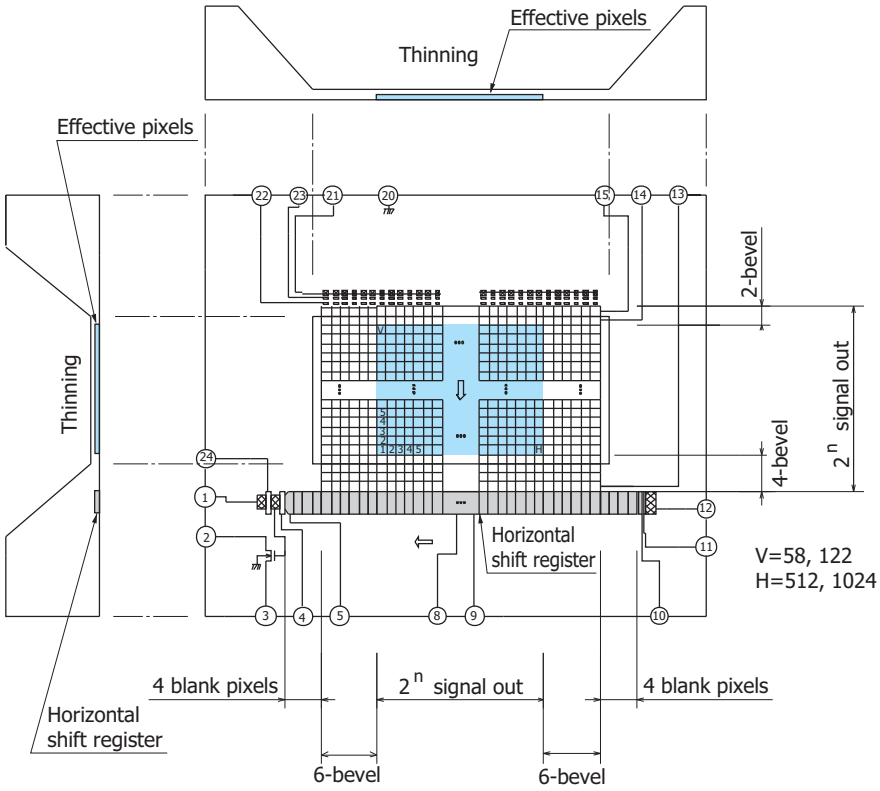
Device structure (conceptual drawing of top view)



Note: When viewed from the direction of the incident light, the horizontal shift register is covered with a thick silicon layer (dead layer). However, long-wavelength light passes through the silicon dead layer and may possibly be detected by the horizontal shift register. To prevent this, provide light shield on that area as needed.

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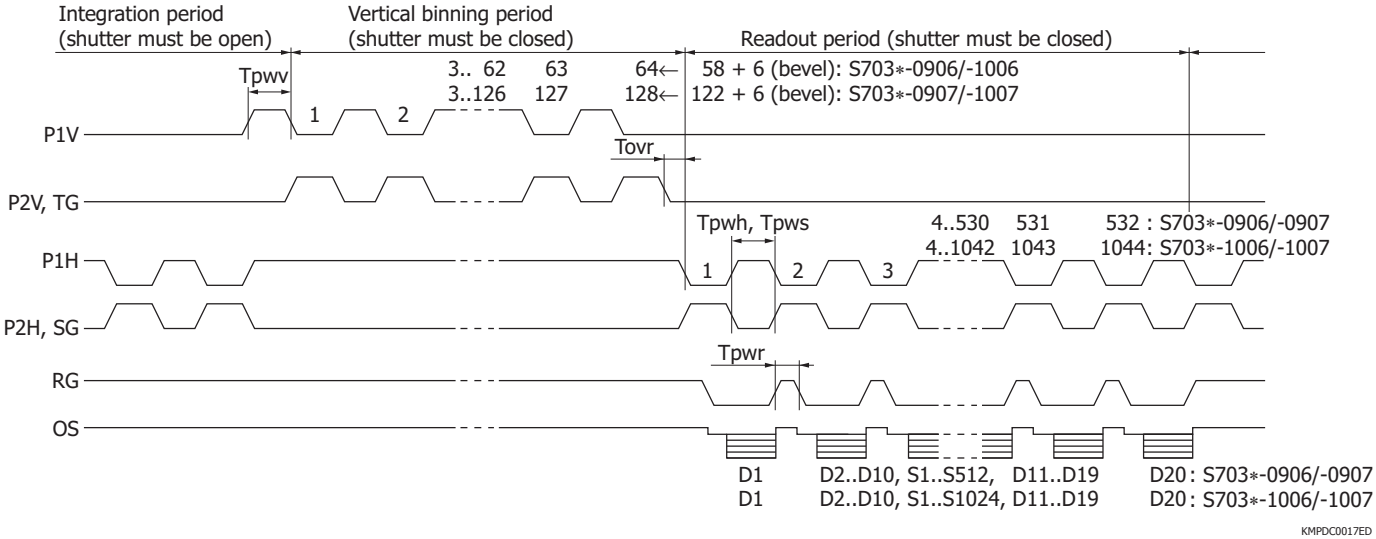
Timing chart

Line binning



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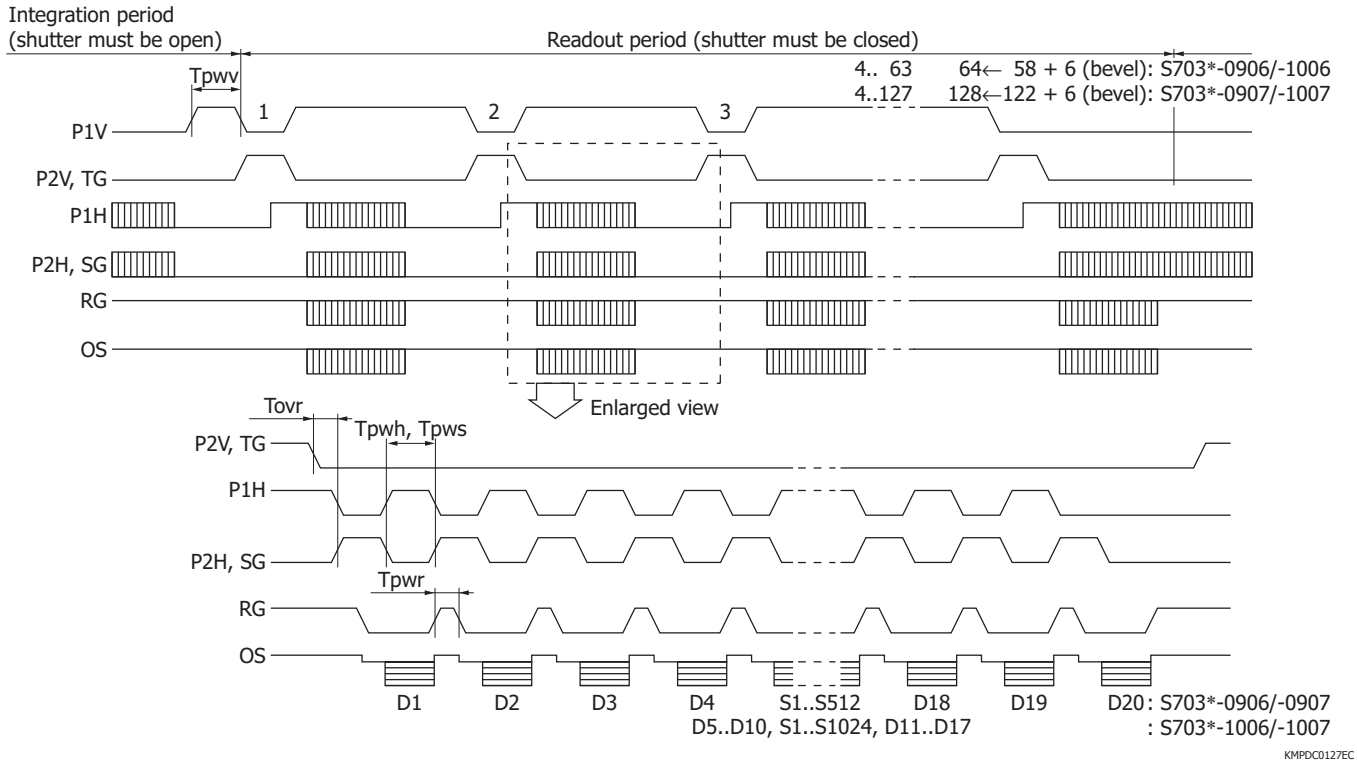
Parameter			Symbol	Min.	Typ.	Max.	Unit
P1V, P2V, TG*17	Pulse width	S703∗-0906	Tpwv	1.5	2	-	µs
		S703∗-0907/-1006		3	4	-	
		S703∗-1007		6	8	-	
	Rise and fall time		Tprv, Tpfv	10	-	-	ns
P1H, P2H*17	Pulse width		Tpwh	500	2000	-	ns
	Rise and fall time		Tprh, Tpfh	10	-	-	ns
	Duty ratio		-	-	50	-	%
SG	Pulse width		Tpws	500	2000	-	ns
	Rise and fall time		Tprs, Tpfs	10	-	-	ns
	Duty ratio		-	-	50	-	%
RG	Pulse width		Tpwr	100	-	-	ns
	Rise and fall time		Tprr, Tpfr	5	-	-	ns
TG – P1H	Overlap time		Tovr	3	-	-	µs

*17: Symmetrical clock pulses should be overlapped at 50% of maximum pulse amplitude.

Area scanning: large full well mode

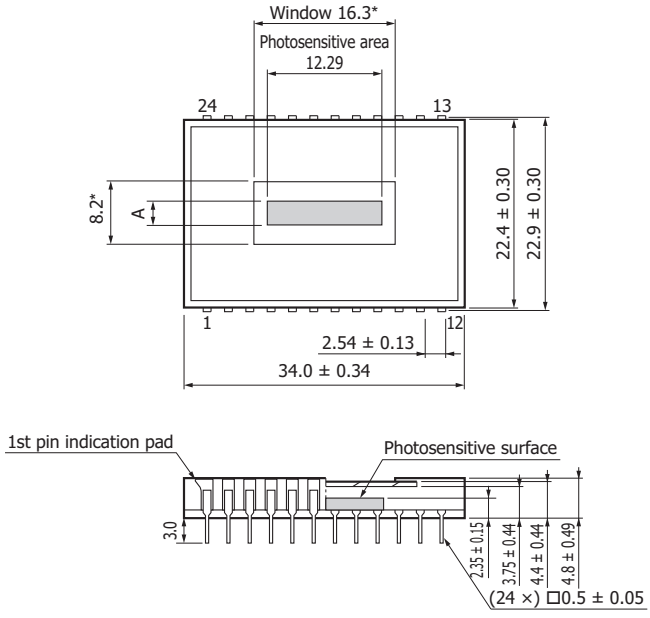


Parameter			Symbol	Min.	Typ.	Max.	Unit
P1V, P2V, TG*18	Pulse width	S703*-0906	Tpwv	1.5	2	-	µs
		S703*-0907/-1006		3	4	-	
		S703*-1007		6	8	-	
	Rise and fall time		Tprv, Tpfv	10	-	-	ns
P1H, P2H*18	Pulse width		Tpwh	500	2000	-	ns
	Rise and fall time		Tprh, Tpfh	10	-	-	ns
	Duty ratio		-	-	50	-	%
SG	Pulse width		Tpws	500	2000	-	ns
	Rise and fall time		Tprs, Tpfs	10	-	-	ns
	Duty ratio		-	-	50	-	%
RG	Pulse width		Tpwr	100	-	-	ns
	Rise and fall time		Tprr, Tpfr	5	-	-	ns
TG – P1H	Overlap time		Tovr	3	-	-	µs

*18: Symmetrical clock pulses should be overlapped at 50% of maximum pulse amplitude.

Dimensional outline (unit: mm)

S7030-0906/-0907



S7030-0906: A=1.392
S7030-0907: A=2.928

* Size of window that guarantees the transmittance in the "Spectral transmittance characteristics" graph

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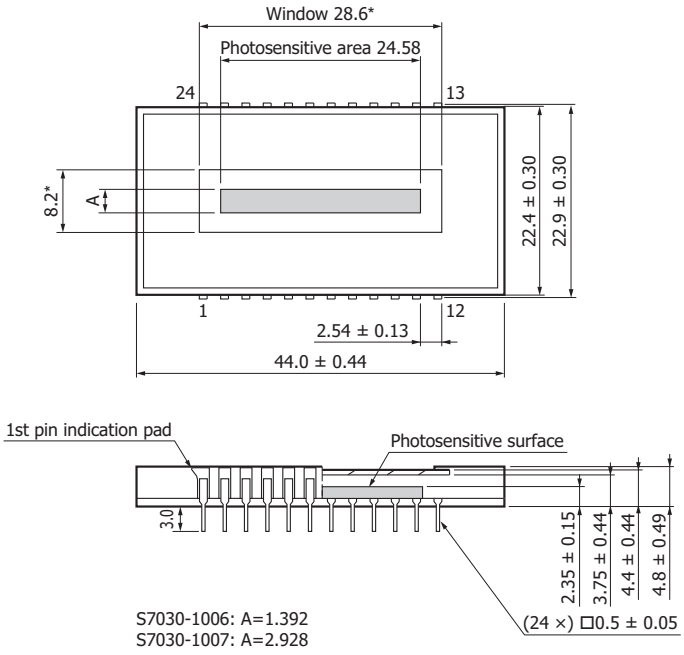
S7030-1006/-1007

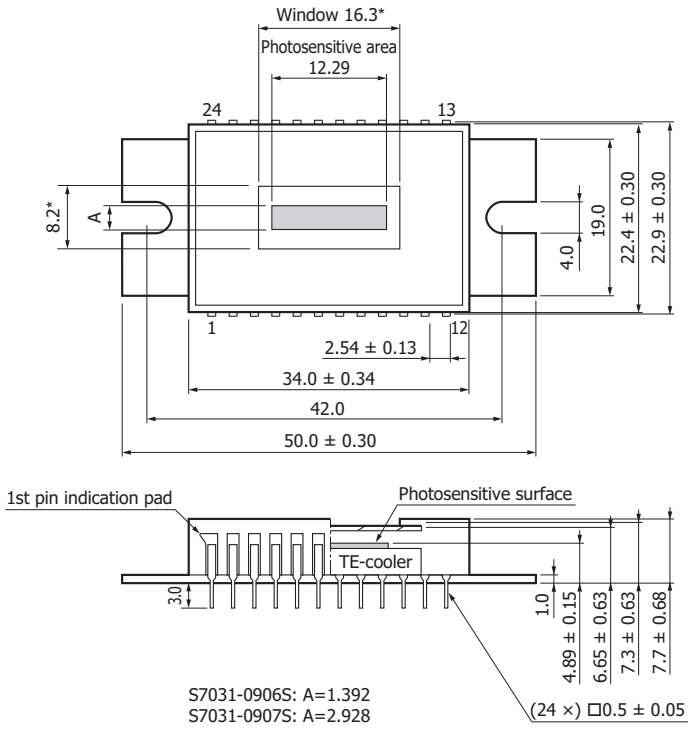


S7030-1006: A=1.392
S7030-1007: A=2.928

* Size of window that guarantees the transmittance in the "Spectral transmittance characteristics" graph

KMPDA0047EG

S7031-0906S/-0907S



S7031-0906S: A=1.392
S7031-0907S: A=2.928

* Size of window that guarantees the transmittance in the "Spectral transmittance characteristics" graph

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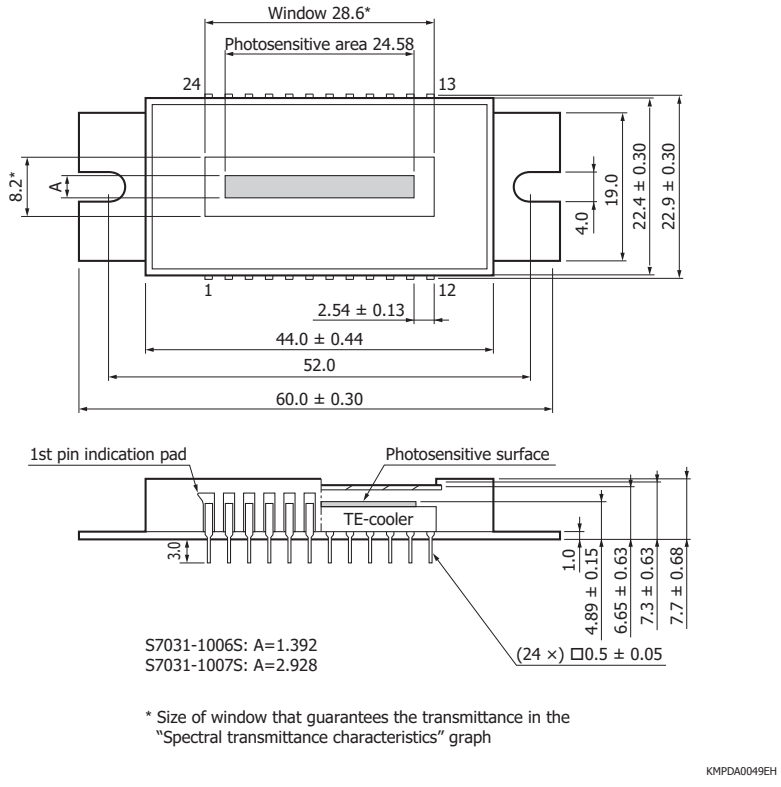
S7031-1006S/-1007S



* Size of window that guarantees the transmittance in the "Spectral transmittance characteristics" graph

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Pin connections

Pin no.	S7030 series		S7031 series		Remark (standard operation)
	Symbol	Function	Symbol	Function	
1	RD	Reset drain	RD	Reset drain	+12 V
2	OS	Output transistor source	OS	Output transistor source	R_L=22 kΩ
3	OD	Output transistor drain	OD	Output transistor drain	+20 V
4	OG	Output gate	OG	Output gate	+3 V
5	SG	Summing gate	SG	Summing gate	Same pulse as P2H
6	-		-		
7	-		-		
8	P2H	CCD horizontal register clock-2	P2H	CCD horizontal register clock-2	
9	P1H	CCD horizontal register clock-1	P1H	CCD horizontal register clock-1	
10	IG2H	Test point (horizontal input gate-2)	IG2H	Test point (horizontal input gate-2)	-8 V
11	IG1H	Test point (horizontal input gate-1)	IG1H	Test point (horizontal input gate-1)	-8 V
12	ISH	Test point (horizontal input source)	ISH	Test point (horizontal input source)	Connect to RD
13	TG*19	Transfer gate	TG*19	Transfer gate	Same pulse as P2V
14	P2V	CCD vertical register clock-2	P2V	CCD vertical register clock-2	
15	P1V	CCD vertical register clock-1	P1V	CCD vertical register clock-1	
16	-		Th1	Thermistor	
17	-		Th2	Thermistor	
18	-		P-	TE-cooler-	
19	-		P+	TE-cooler+	
20	SS	Substrate (GND)	SS	Substrate (GND)	GND
21	ISV	Test point (vertical input source)	ISV	Test point (vertical input source)	Connect to RD
22	IG2V	Test point (vertical input gate-2)	IG2V	Test point (vertical input gate-2)	-8 V
23	IG1V	Test point (vertical input gate-1)	IG1V	Test point (vertical input gate-1)	-8 V
24	RG	Reset gate	RG	Reset gate	

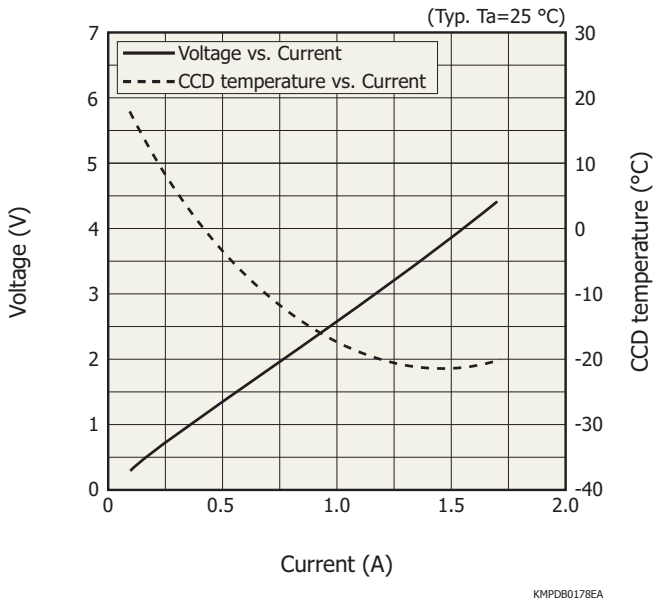
*19: Isolation gate between vertical register and horizontal register. In standard operation, TG should be applied the same pulse as P2V.

Specifications of built-in TE-cooler (Typ. vacuum condition)

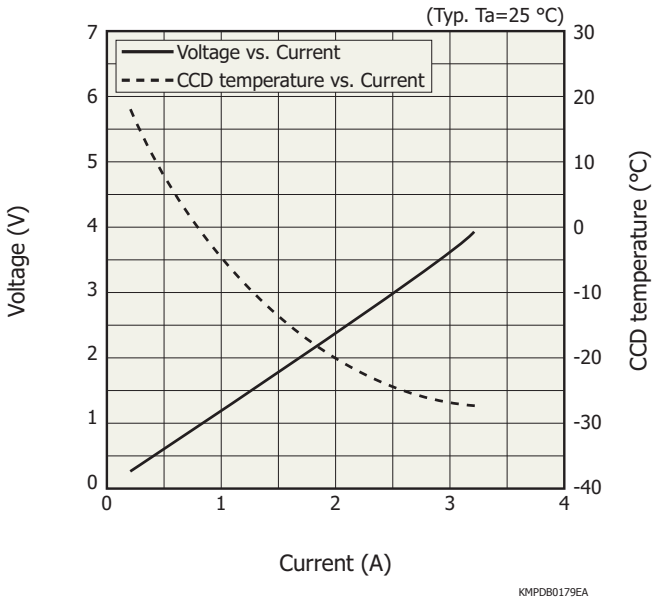
Parameter	Symbol	Condition	S7031-0906S/-0907S	S7031-1006S/-1007S	Unit
Internal resistance	Rint	Ta=25 °C	2.5	1.2	Ω
Maximum current*20	Imax	Tc*21=Th*22=25 °C	1.5	3.0	A
Maximum voltage	Vmax	Tc*21=Th*22=25 °C	3.8	3.6	V
Maximum heat absorption*23	Qmax		3.4	5.1	W
Maximum temperature of heat radiating side	-		70	70	°C

*20: If the current greater than this value flows into the thermoelectric cooler, the heat absorption begins to decrease due to the Joule heat. It should be noted that this value is not the damage threshold value. To protect the thermoelectric cooler and maintain stable operation, the supply current should be less than 60% of this maximum current.
*21: Temperature of the cooling side of thermoelectric cooler
*22: Temperature of the heat radiating side of thermoelectric cooler
*23: This is a theoretical heat absorption level that offsets the temperature difference in the thermoelectric cooler when the maximum current is supplied to the unit.

S7031-0906S/-0907S



S7031-1006S/-1007S

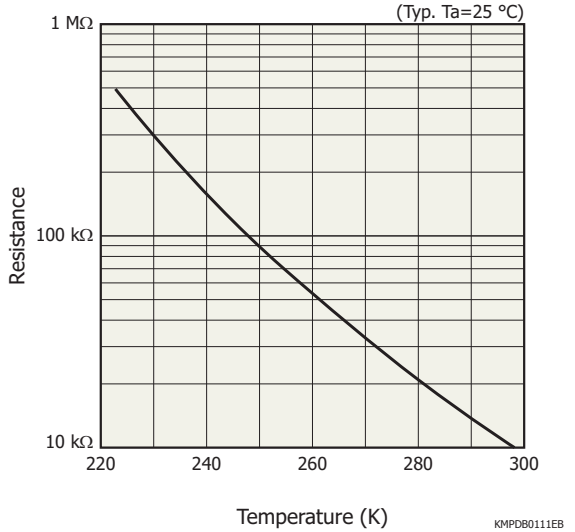


Specifications of built-in temperature sensor

A thermistor chip is built in the same package with a CCD chip, and the CCD chip temperature can be monitored with it. A relation between the thermistor resistance and absolute temperature is expressed by the following equation.

$R_{T1} = R_{T2} \times \exp B_{T1/T2} (1/T1 - 1/T2)$
R_{T1}: Resistance at absolute temperature T1 [K]
R_{T2}: Resistance at absolute temperature T2 [K]
$B_{T1/T2}$: B constant [K]

The characteristics of the thermistor used are as follows.
R_{298}=10 kΩ
$B_{298/323}$=3450 K



Precautions (electrostatic countermeasures)

- Handle these sensors with bare hands or wearing cotton gloves. In addition, wear anti-static clothing or use a wrist band with an earth ring, in order to prevent electrostatic damage due to electrical charges from friction.
- Avoid directly placing these sensors on a work-desk or work-bench that may carry an electrostatic charge.
- Provide ground lines or ground connection with the work-floor, work-desk and work-bench to allow static electricity to discharge.
- Ground the tools used to handle these sensors, such as tweezers and soldering irons.

It is not always necessary to provide all the electrostatic measures stated above. Implement these measures according to the amount of damage that occurs.

Element cooling/heating temperature incline rate

When cooling the CCD by an externally attached cooler, set the cooler operation so that the temperature gradient (rate of temperature change) for cooling or allowing the CCD to warm back is less than 5 K/minute.

Related information

www.hamamatsu.com/sp/ssd/doc_en.html

■ Precautions

- Notice
- Image sensors/Precautions

■ Technical information

- FFT-CCD area image sensor/Technical information

Multichannel detector heads C7040, C7041

Features

- **C7040: for S7030 series**
  C7041: for S7031 series
- **Area scanning or full line-binnng operation**
- **Readout frequency: 250 kHz**
- **Readout noise: 20 e^- rms**
- **ΔT=50 °C (ΔT changes by cooling method.)**

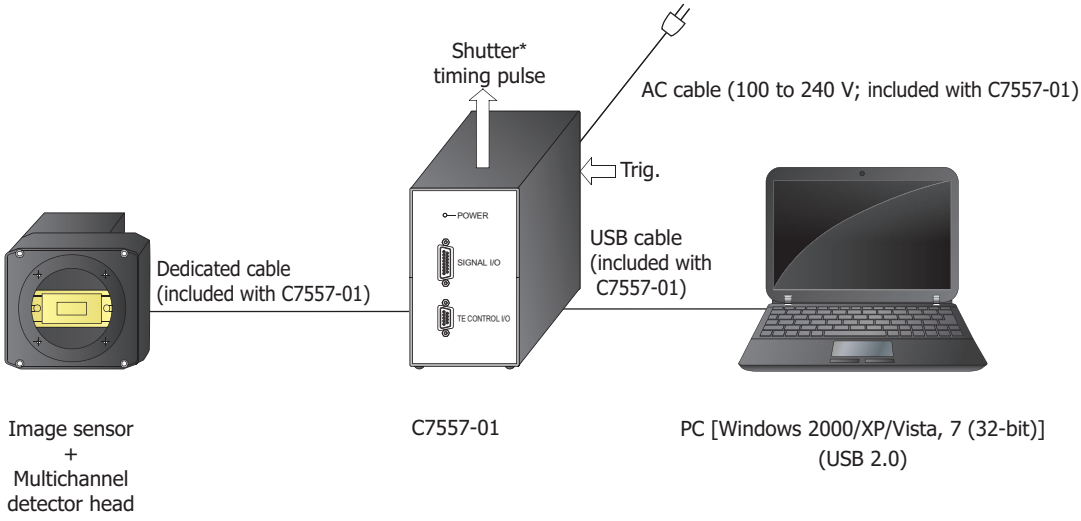
Input	Symbol	Value
Supply voltage	V_{D1}	+5 Vdc, 200 mA
	V_{A1+}	+15 Vdc, +100 mA
	V_{A1-}	-15 Vdc, -100 mA
	V_{A2}	+24 Vdc, 30 mA
	V_{D2}	+5 Vdc, 30 mA (C7041)
	Vp	+5 Vdc, 2.5 A (C7041)
	V_F	+12 Vdc, 100 mA (C7041)
Master start	ϕms	HCMOS logic compatible
Master clock	ϕmc	HCMOS logic compatible, 1 MHz

Multichannel detector head controller C7557-01

Features

- **For control of multichannel detector head and data acquisition**
- **Easy control and data acquisition using supplied software via USB interface**

Connection example



* Shutter, etc. are not available.

KACCC0402EC

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Cat. No. KMPD1023E18 Aug. 2012 DN